

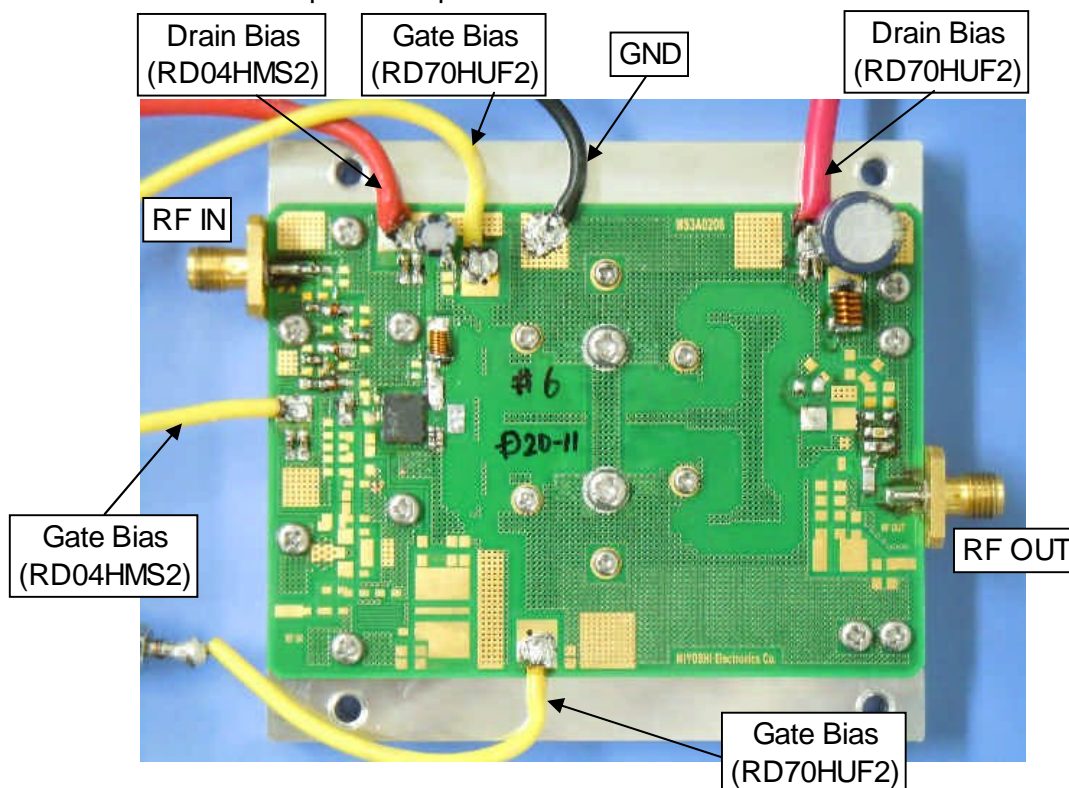
# APPLICATION NOTE

Document NO. AN-UHF-122  
Date : 28<sup>th</sup> Feb. 2011  
Prepared : Y.Takase  
S.Kametani  
Confirmed : T.Okawa  
(Taking charge of Silicon RF by  
MIYOSHI Electronics)

**SUBJECT:** RD04HMS2 & RD70HUF2 two-stage amplifier at  $f=380\text{-}470\text{MHz}$ . ( $V_{dd}=12.5\text{V}$ )

## Features:

- The evaluation board for RD04HMS2 & RD70HUF2 two-stage amplifier
- Frequency: 380-470MHz
- Vdd: 12.5V
- Input power: 0.2W
- Output power: 79-88W
- Quiescent Current: RD04HMS2 ; 0.1A, RD70HUF2 ; 1A
- Operating Current: 12-13A
- Surface-mounted RF power amplifier structure

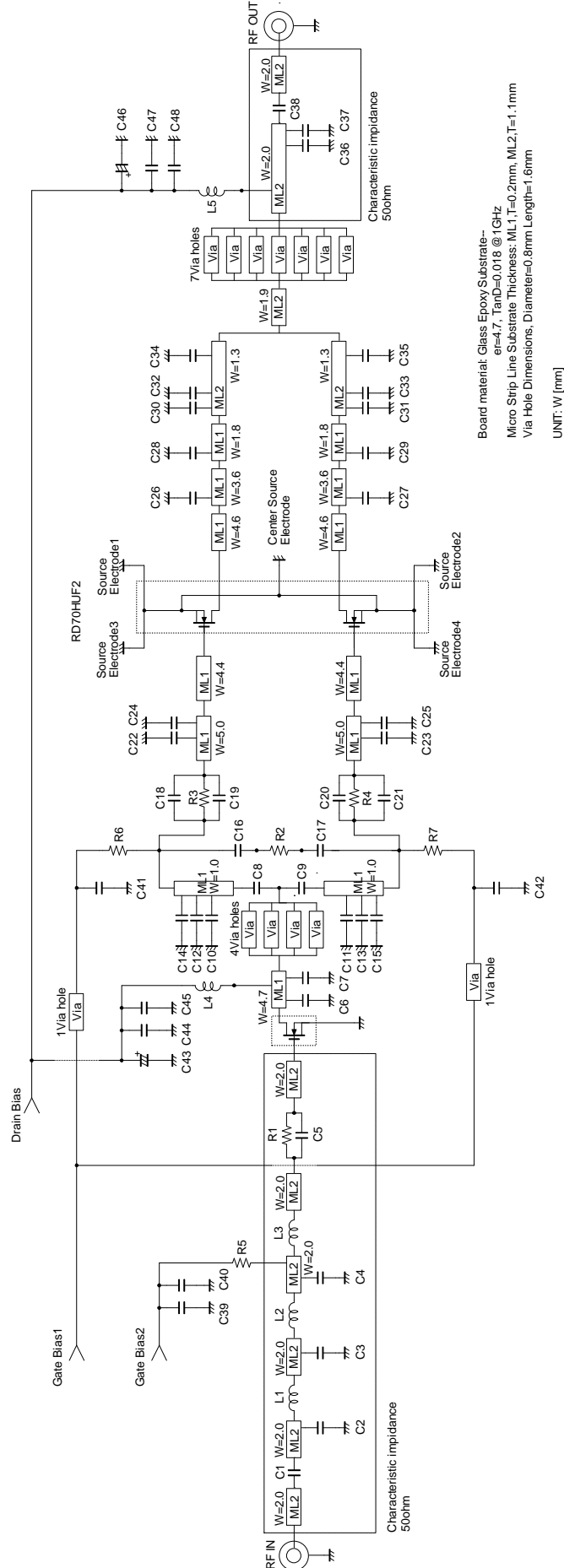


PCB L=82.5mm W=60.0mm

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1. Equivalent Circuitry



## 2. Component List and Standard Deliverable

## - Component List

No.	Description	P/N	Qty	Manufacturer
Tr 1	MOSFET	RD04HMS2	1	Mitsubishi Electric Corporation
Tr 2	MOSFET	RD70HUF2	1	Mitsubishi Electric Corporation

No.	Description			P/N	Qty	Manufacturer
	Capacitance	Size	Remarks			
C 1	100 pF	1608	50 V	GRM1882C1H101JA01D	1	MURATA MANUFACTURING CO.
C 2	6.2 pF	1608	Hi-Q 100 V	GQM1882C2A6R2CB01D	1	MURATA MANUFACTURING CO.
C 3	22 pF	1608	Hi-Q 50 V	GQM1882C1H220JB01D	1	MURATA MANUFACTURING CO.
C 4	36 pF	1608	Hi-Q 50 V	GQM1882C1H360JB01D	1	MURATA MANUFACTURING CO.
C 5	24 pF	1608	Hi-Q 50 V	GQM1882C1H240JB01D	1	MURATA MANUFACTURING CO.
C 6	27 pF	1608	Hi-Q 50 V	GQM1882C1H270JB01D	1	MURATA MANUFACTURING CO.
C 7	27 pF	1608	Hi-Q 50 V	GQM1882C1H270JB01D	1	MURATA MANUFACTURING CO.
C 8	100 pF	1608	50 V	GRM1882C1H101JA01D	1	MURATA MANUFACTURING CO.
C 9	100 pF	1608	50 V	GRM1882C1H101JA01D	1	MURATA MANUFACTURING CO.
C 10	22 pF	1608	Hi-Q 50 V	GQM1882C1H220JB01D	1	MURATA MANUFACTURING CO.
C 11	22 pF	1608	Hi-Q 50 V	GQM1882C1H220JB01D	1	MURATA MANUFACTURING CO.
C 12	22 pF	1608	Hi-Q 50 V	GQM1882C1H220JB01D	1	MURATA MANUFACTURING CO.
C 13	22 pF	1608	Hi-Q 50 V	GQM1882C1H220JB01D	1	MURATA MANUFACTURING CO.
C 14	22 pF	1608	Hi-Q 50 V	GQM1882C1H220JB01D	1	MURATA MANUFACTURING CO.
C 15	22 pF	1608	Hi-Q 50 V	GQM1882C1H220JB01D	1	MURATA MANUFACTURING CO.
C 16	910 pF	2012	50 V	GRM2162C1H911JA01D	1	MURATA MANUFACTURING CO.
C 17	910 pF	2012	50 V	GRM2162C1H911JA01D	1	MURATA MANUFACTURING CO.
C 18	62 pF	2012	Hi-Q 250 V	GQM2195C2E620JB12D	1	MURATA MANUFACTURING CO.
C 19	62 pF	2012	Hi-Q 250 V	GQM2195C2E620JB12D	1	MURATA MANUFACTURING CO.
C 20	62 pF	2012	Hi-Q 250 V	GQM2195C2E620JB12D	1	MURATA MANUFACTURING CO.
C 21	62 pF	2012	Hi-Q 250 V	GQM2195C2E620JB12D	1	MURATA MANUFACTURING CO.
C 22	8.2 pF	1608	Hi-Q 50 V	GQM1882C1H8R2CB01D	1	MURATA MANUFACTURING CO.
C 23	8.2 pF	1608	Hi-Q 50 V	GQM1882C1H8R2CB01D	1	MURATA MANUFACTURING CO.
C 24	9.1 pF	1608	Hi-Q 50 V	GQM1882C1H9R1CB01D	1	MURATA MANUFACTURING CO.
C 25	9.1 pF	1608	Hi-Q 50 V	GQM1882C1H9R1CB01D	1	MURATA MANUFACTURING CO.
C 26	43 pF	2012	Hi-Q 250 V	GQM2195C2E430JB12D	1	MURATA MANUFACTURING CO.
C 27	43 pF	2012	Hi-Q 250 V	GQM2195C2E430JB12D	1	MURATA MANUFACTURING CO.
C 28	43 pF	2012	Hi-Q 250 V	GQM2195C2E430JB12D	1	MURATA MANUFACTURING CO.
C 29	43 pF	2012	Hi-Q 250 V	GQM2195C2E430JB12D	1	MURATA MANUFACTURING CO.
C 30	12 pF	2012	Hi-Q 250 V	GQM2195C2E120JB12D	1	MURATA MANUFACTURING CO.
C 31	12 pF	2012	Hi-Q 250 V	GQM2195C2E120JB12D	1	MURATA MANUFACTURING CO.
C 32	24 pF	2012	Hi-Q 250 V	GQM2195C2E240JB12D	1	MURATA MANUFACTURING CO.
C 33	24 pF	2012	Hi-Q 250 V	GQM2195C2E240JB12D	1	MURATA MANUFACTURING CO.
C 34	7.5 pF	2012	Hi-Q 250 V	GQM2195C2E7R5CB12D	1	MURATA MANUFACTURING CO.
C 35	7.5 pF	2012	Hi-Q 250 V	GQM2195C2E7R5CB12D	1	MURATA MANUFACTURING CO.
C 36	2.7 pF	2012	Hi-Q 250 V	GQM2195C2E2R7CB12D	1	MURATA MANUFACTURING CO.
C 37	2.7 pF	2012	Hi-Q 250 V	GQM2195C2E2R7CB12D	1	MURATA MANUFACTURING CO.
C 38	330 pF	3216	200 V	GRM31M2C2D331JY21B	1	MURATA MANUFACTURING CO.
C 39	10000 pF	1608	50 V	GRM188B11H103KA01	1	MURATA MANUFACTURING CO.
C 40	1000 pF	1608	50 V	GRM1882C1H102JA01	1	MURATA MANUFACTURING CO.
C 41	1000 pF	1608	50 V	GRM1882C1H102JA01	1	MURATA MANUFACTURING CO.
C 42	1000 pF	1608	50 V	GRM1882C1H102JA01	1	MURATA MANUFACTURING CO.
C 43	22 μF	-	50 V	H1002	1	NICHICON Corporation
C 44	10000 pF	1608	50 V	GRM188B11H103KA01	1	MURATA MANUFACTURING CO.
C 45	1000 pF	1608	50 V	GRM1882C1H102JA01	1	MURATA MANUFACTURING CO.
C 46	220 μF	-	35 V	EEUFC1V221	1	Panasonic Corporation
C 47	910 pF	2012	50 V	GRM2162C1H911JA01D	1	MURATA MANUFACTURING CO.
C 48	910 pF	2012	50 V	GRM2162C1H911JA01D	1	MURATA MANUFACTURING CO.

**RD04HMS2 & RD70HUF2 two-stage amplifier at 380-470MHz. (Vdd=12.5V)**

**- AN-UHF-122 -**

\* Inductor of Rolling Coil measurement condition : f=100MHz

No.	Description					P/N	Qty	Manufacturer	Remarks
	Inductance	Diameter			T/N of coils				
		Wire Φ	Inside Φ						
L	1	12 nH *	0.23 mm	1.1 mm	3	2303A	1	YC Corporation Co.,Ltd.	Enameled wire
L	2	8 nH *	0.23 mm	1.1 mm	2	2302S	1	YC Corporation Co.,Ltd.	Enameled wire
L	3	8 nH *	0.23 mm	1.1 mm	2	2302S	1	YC Corporation Co.,Ltd.	Enameled wire
L	4	37 nH *	0.40 mm	1.6 mm	7	4007C	1	YC Corporation Co.,Ltd.	Enameled wire
L	5	25 nH *	0.80 mm	2.2 mm	5	8005C	1	YC Corporation Co.,Ltd.	Enameled wire

No.	Description		P/N	Qty	Manufacturer
	Resistance	Size			
R	1	47 ohm	1608	1	TAIYOSHA ELECTRIC CO.
R	2	2.2 ohm	2012	1	TAIYOSHA ELECTRIC CO.
R	3	100 ohm	2012	1	TAIYOSHA ELECTRIC CO.
R	4	100 ohm	2012	1	TAIYOSHA ELECTRIC CO.
R	5	3900 ohm	1608	1	TAIYOSHA ELECTRIC CO.
R	6	2700 ohm	1608	1	TAIYOSHA ELECTRIC CO.
R	7	2700 ohm	1608	1	TAIYOSHA ELECTRIC CO.

No.	Description	P/N	Qty	Manufacturer
Pb	PCB	MS3A0208	1	Homebuilt
√ OPTION				
Rc	SMA female connector	PAF-S00-002	2	GIGALANE Corporation
Bc	Bias connector red color	TM-605R	2	MSK Corporation
Bc	Bias connector black color	TM-605B	2	MSK Corporation
Pe	Aluminum pedestal	-	1	Homebuilt
Pd	Thermal Silicon Compound	G746	-	Shin-Etsu Chemical Co.,Ltd
Cu	Copper plate 2.8 x 1.8 x 0.4t (mm)	-	1	Homebuilt
	Conducting wire	-	6	Homebuilt
	Screw M3	-	2	-
	Screw M2.6	-	10	-
	Screw M2	-	10	-

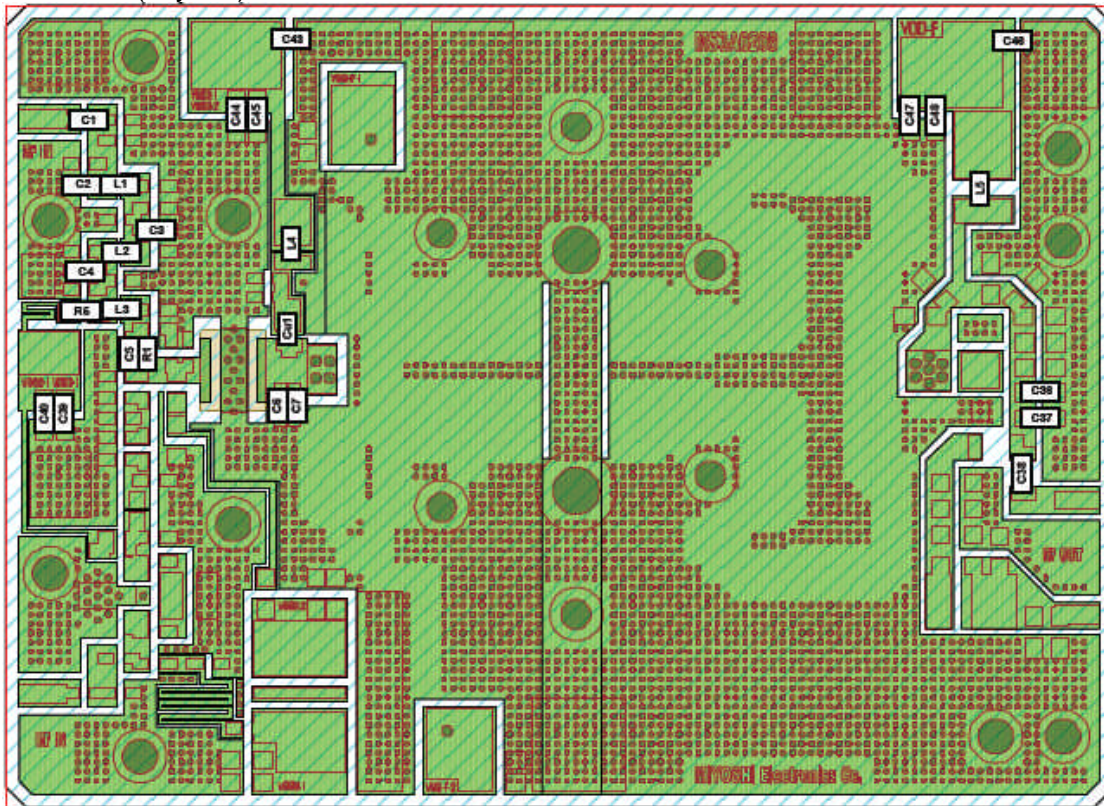
**- Standard Deliverable**

TYPE1	Evaluation Board assembled with all the component
TYPE2	PCB (raw board)

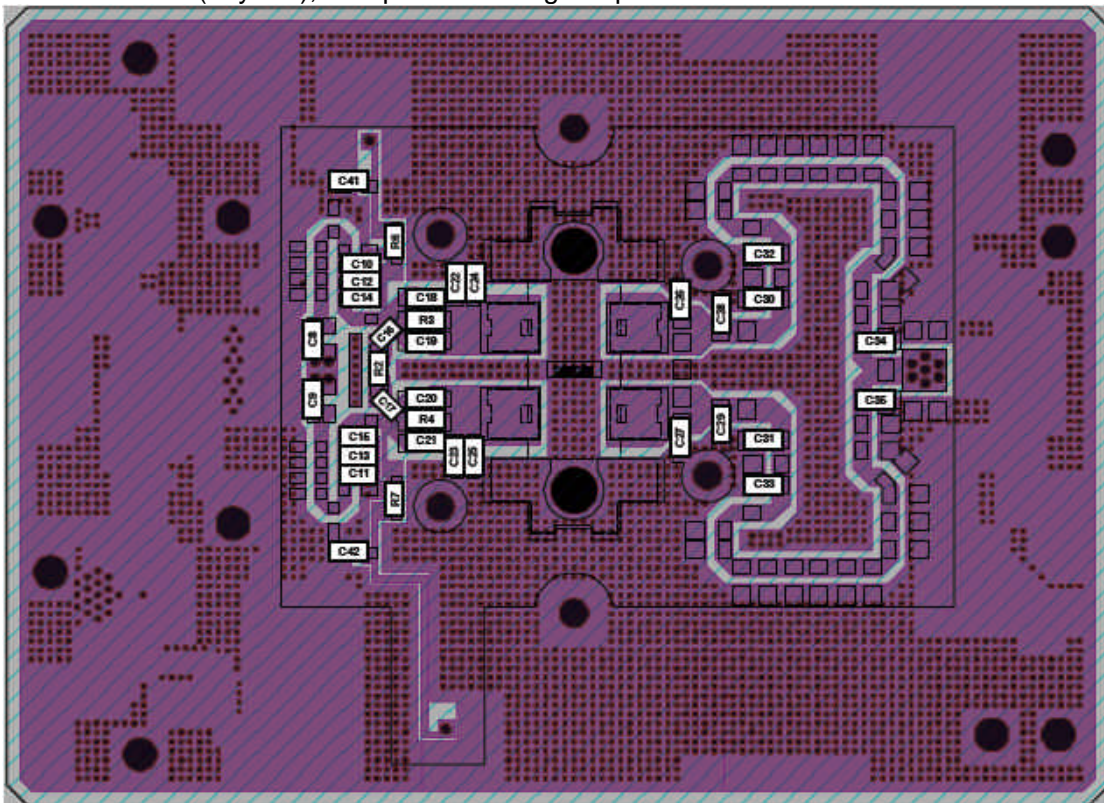
### 3. PCB Layout

BOARD OUTLINE: 82.5\*60.0(mm)

TOP VIEW (Layer 1)

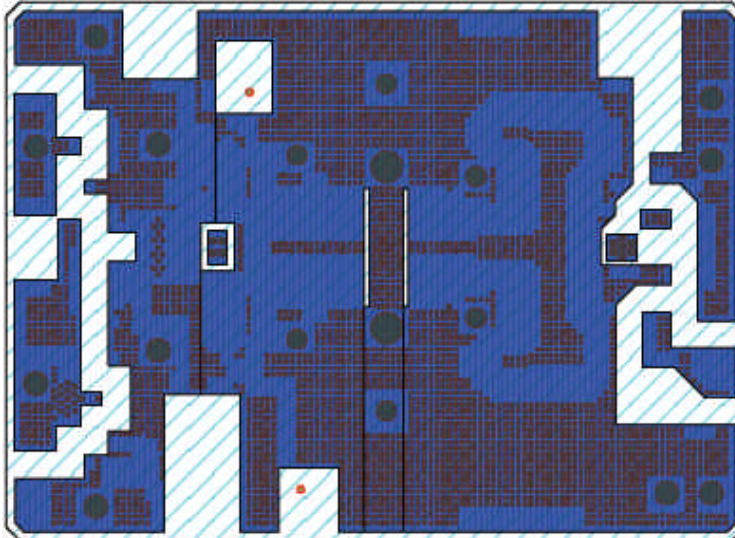


BOTTOM VIEW (Layer 6), Perspective through Top View

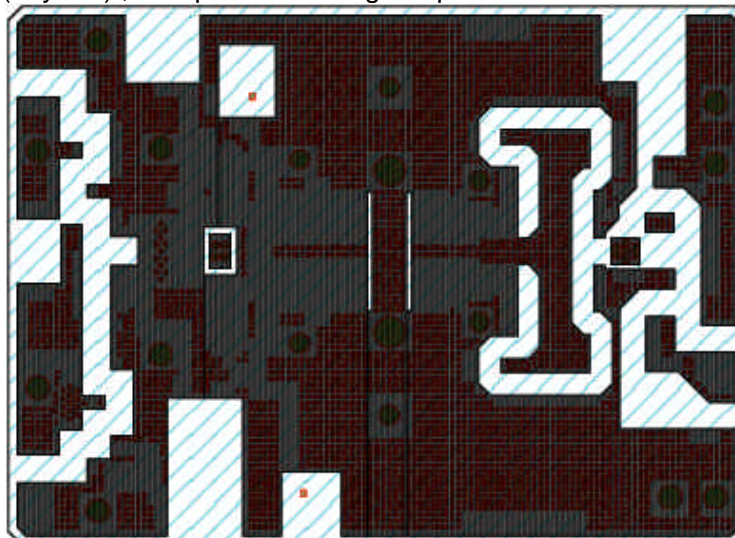


BOARD OUTLINE: 82.5\*60.0(mm)

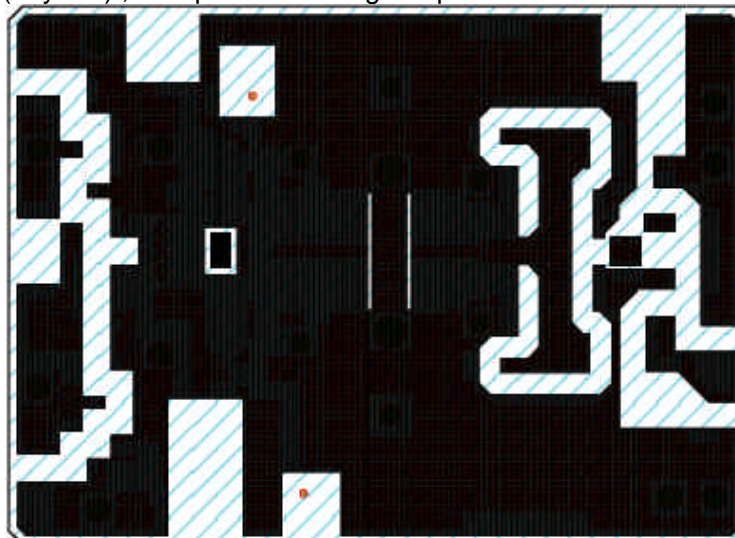
Internal Layer (Layer 2) , Perspective Through Top View



Internal Layer (Layer 3) , Perspective Through Top View

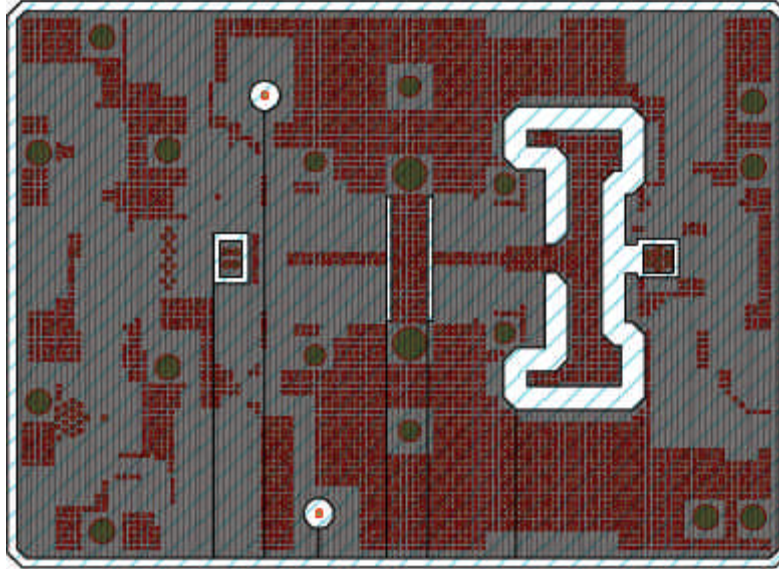


Internal Layer (Layer 4) , Perspective Through Top View



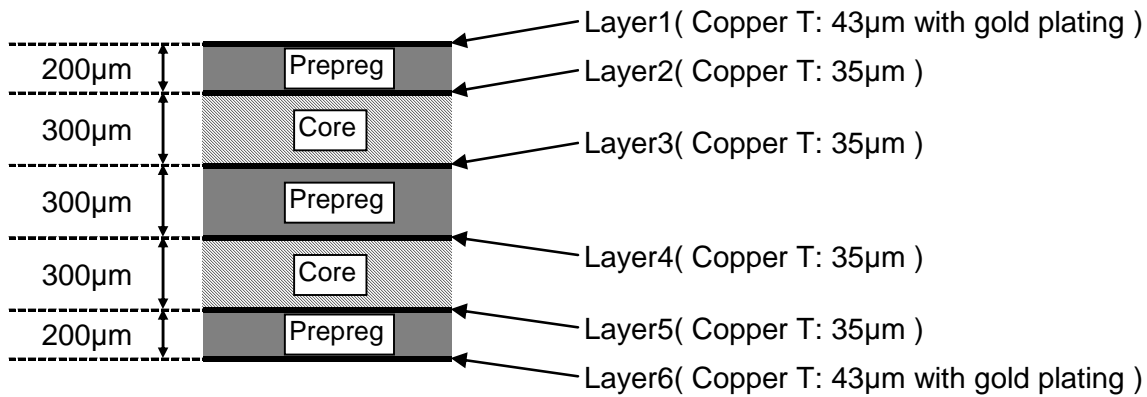
BOARD OUTLINE: 82.5\*60.0(mm)

Internal Layer (Layer 5) , Perspective Through Top View



Substrate Condition

Nominal Total Completed Thickness ( included resist coating ) : 1.6mm



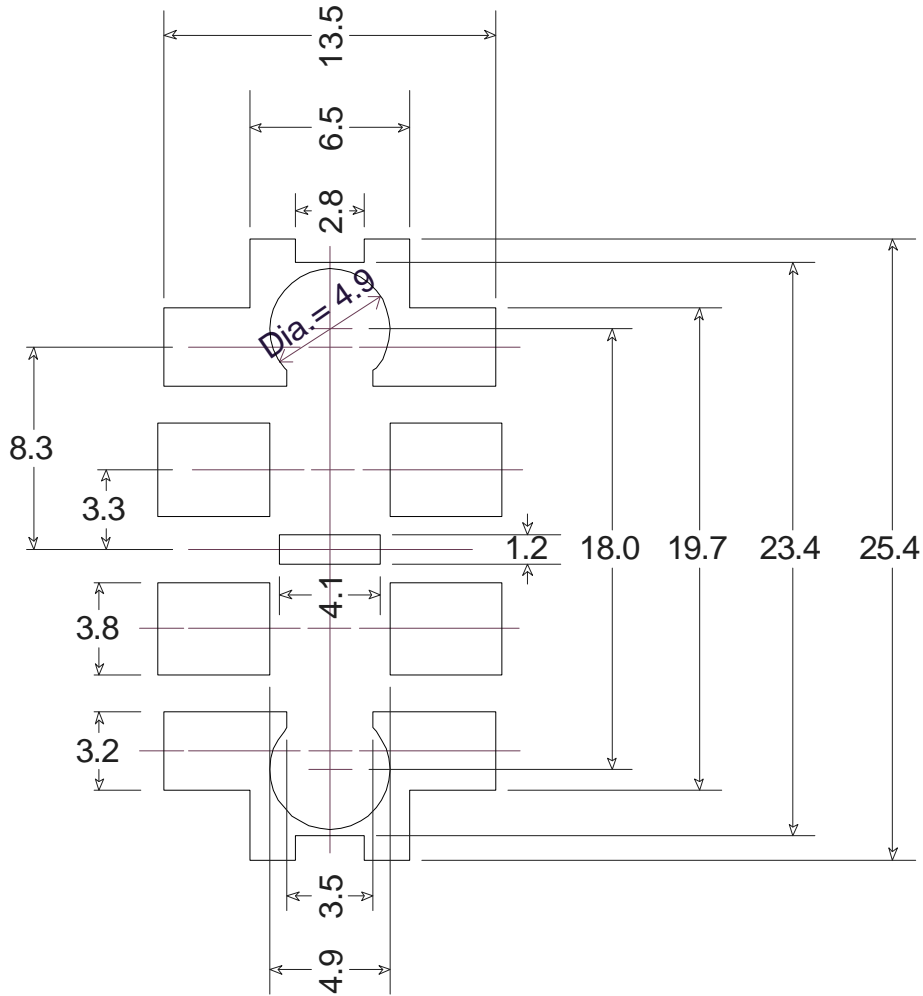
er: 4.7, TanD:0.018 @1GHz

Material: MCL-E-679G(R), Hitachi Chemical Co.



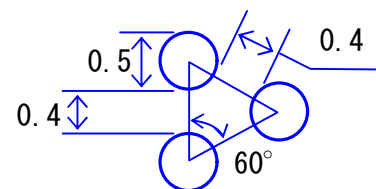
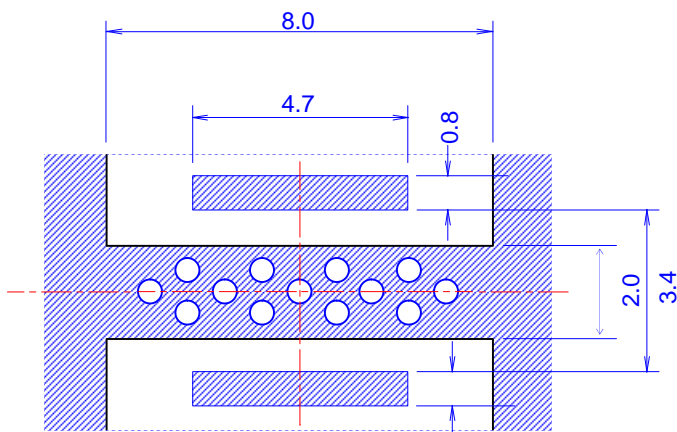
4. Standard Land Pattern Dimensions

4-1. RD70HUF2



UNIT: mm

4-2. RD04HMS2



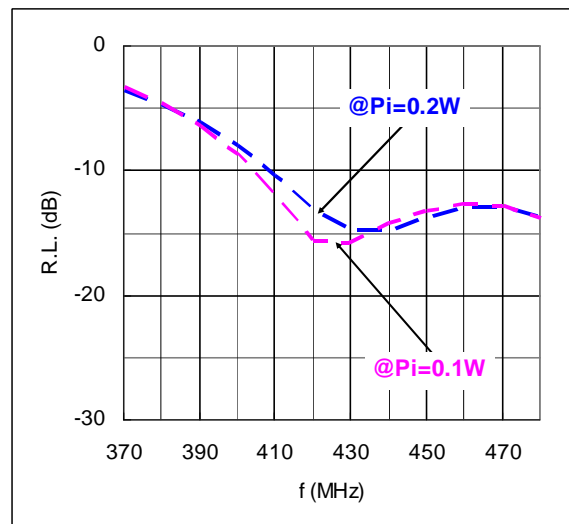
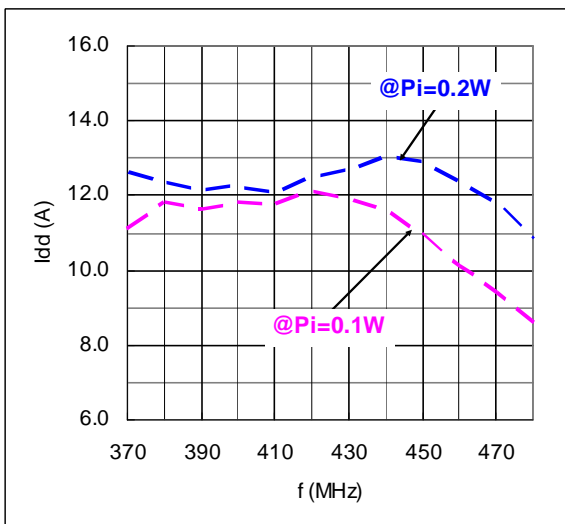
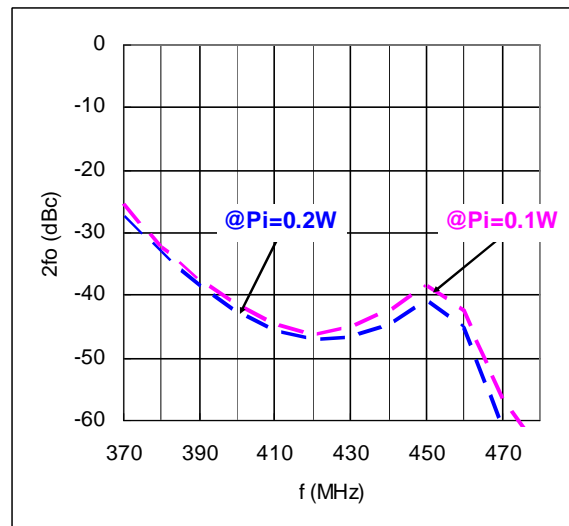
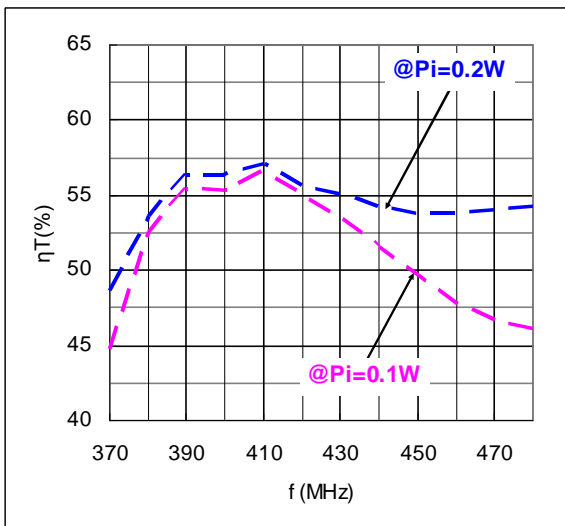
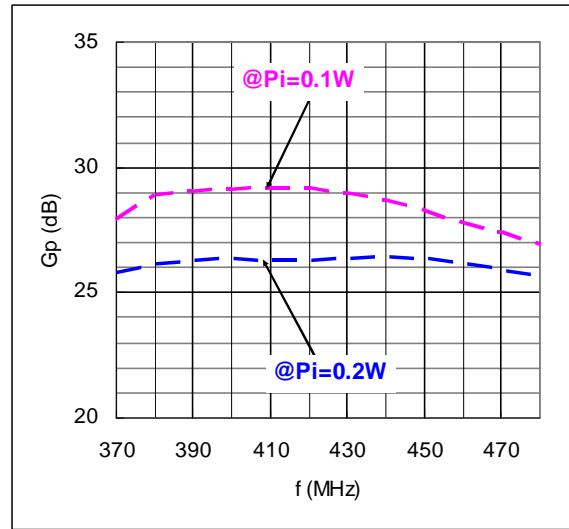
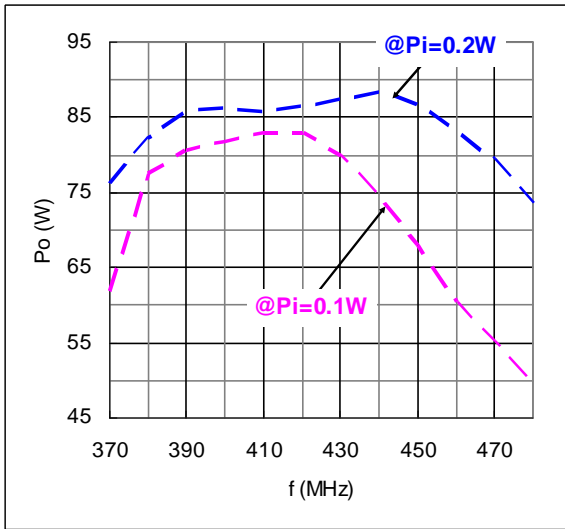
REGULAR TRIANGLE ARRANGEMENT  
THROUGH HOLE

UNIT: mm

## 5. Typical RF Characteristics

### 5-1. Frequency characteristics

@ **Pin Control** (@Pi=0.2W, 0.1W), Vdd=12.5V, Idq=1.1A (Vgg=2.67V)



## 5-1-1. Frequency characteristics data

@  $P_i=0.2W$ , Vdd=12.5V, Idq=1.1A (Vgg=2.67V, RD04HMS2 ; 0.1A, RD70HUF2 ; 1A)

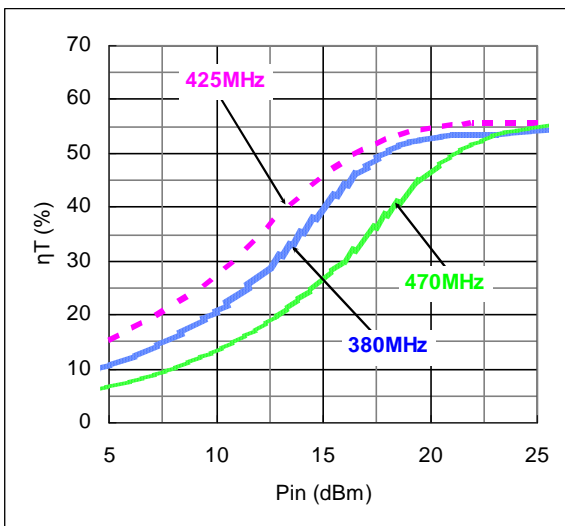
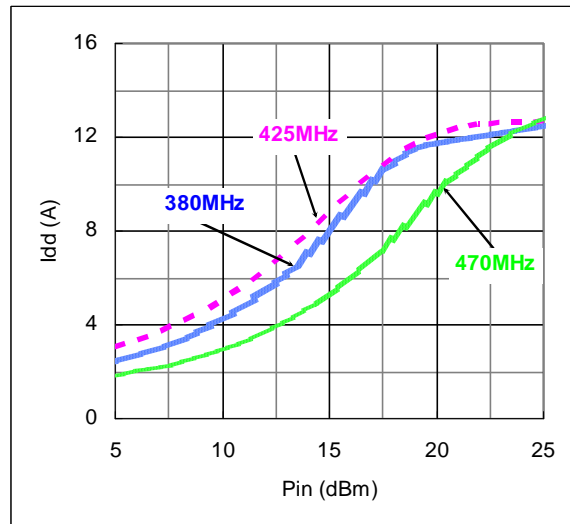
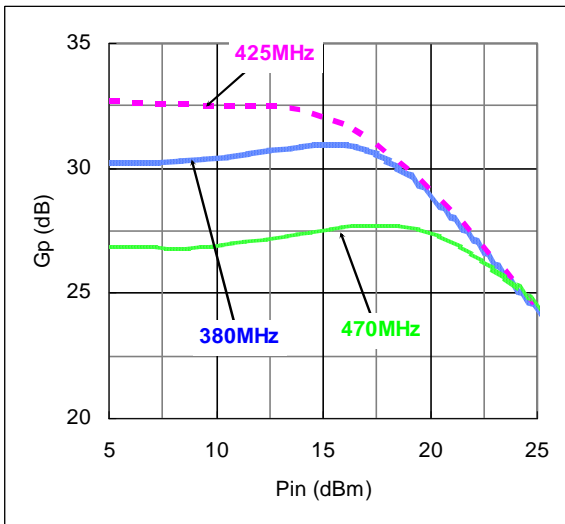
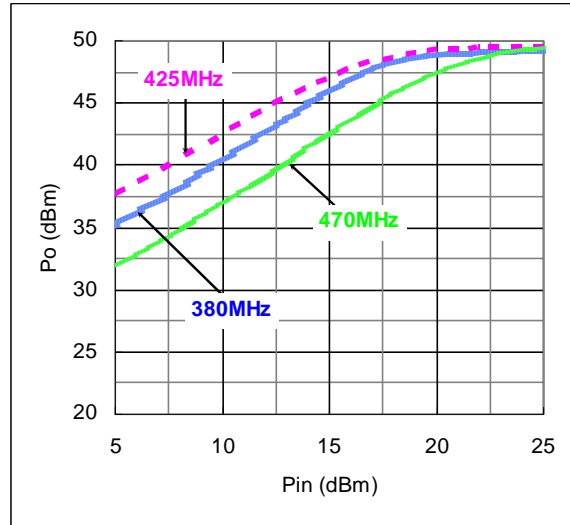
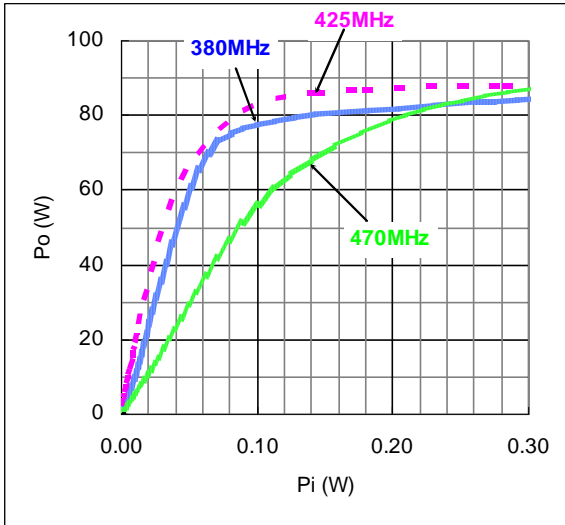
f (MHz)	Po (W)	Po (dBm)	Gp (dB)	Idd (A)	$\eta_T$ (%)	2fo (dBc)	3fo (dBc)	R.L. (dB)
380	82.2	49.2	26.1	12.3	53.5	-33	-69.1	-4.7
390	85.7	49.3	26.3	12.2	56.3	-38	-69.2	-6.1
400	86.3	49.4	26.3	12.3	56.4	-43	-69.3	-7.9
410	85.7	49.3	26.3	12.1	57.1	-46	-69.3	-10.4
420	86.5	49.4	26.3	12.5	55.6	-47	-69.1	-13.0
430	87.5	49.4	26.4	12.7	55.1	-47	-69.2	-14.7
440	88.3	49.5	26.4	13.1	54.3	-45	-69.3	-14.9
450	86.7	49.4	26.4	12.9	53.8	-41	-69.2	-13.8
460	83.0	49.2	26.2	12.4	53.8	-45	-68.4	-13.0
470	79.4	49.0	26.0	11.8	54.0	-61	-68.6	-12.9

@  $P_i=0.1W$ , Vdd=12.5V, Idq=1.1A (Vgg=2.67V, RD04HMS2 ; 0.1A, RD70HUF2 ; 1A)

f (MHz)	Po (W)	Po (dBm)	Gp (dB)	Idd (A)	$\eta_T$ (%)	2fo (dBc)	3fo (dBc)	R.L. (dB)
380	77.4	48.9	28.9	11.8	52.5	-32	-68.8	-4.6
390	80.5	49.1	29.0	11.6	55.5	-38	-68.9	-6.4
400	81.8	49.1	29.1	11.8	55.3	-42	-69.0	-8.7
410	83.0	49.2	29.2	11.8	56.7	-45	-69.1	-12.0
420	83.0	49.2	29.2	12.1	55.0	-46	-69.1	-15.6
430	79.8	49.0	29.0	11.9	53.6	-45	-68.8	-15.8
440	74.5	48.7	28.7	11.6	51.6	-42	-68.6	-14.2
450	67.8	48.3	28.3	10.9	49.7	-38	-68.1	-13.3
460	60.4	47.8	27.8	10.1	47.8	-42	-67.2	-12.7
470	55.1	47.4	27.4	9.4	46.8	-57	-66.8	-12.8

### 5-2. Pout vs. Pin characteristics

@ Vdd=12.5V, Idq=1.1A (Vgg=2.67V), f=380MHz, 425MHz, 470MHz



**5-2-2. Pout vs. Pin characteristics data**

[Conditions ; Vdd=12.5V, Idq=1.1A (Vgg=2.67V, RD04HMS2 ; 0.1A, RD70HUF2 ; 1A)]

**@ f=380MHz**

Pi (W)	Pi (dBm)	Po (W)	Po (dBm)	Gp (dB)	Idd (A)	$\eta_T$ (%)	2fo (dBc)	3fo (dBc)	R.L. (dB)
0.003	5.1	3.44	35.4	30.3	2.50	10.9	-28	< -50	-5.0
0.005	7.3	5.69	37.6	30.3	3.11	14.5	-28	< -50	-4.5
0.009	9.5	9.7	39.9	30.4	3.98	19.2	-27	< -60	-4.2
0.014	11.5	16.3	42.1	30.6	5.11	25.3	-27	< -60	-4.1
0.023	13.5	27.4	44.4	30.8	6.59	33.0	-27	< -60	-4.1
0.036	15.6	45.3	46.6	31.0	8.58	42.0	-28	< -60	-4.1
0.057	17.5	65.3	48.2	30.6	10.6	49.3	-31	< -60	-4.2
0.090	19.5	76.7	48.9	29.3	11.7	52.4	-32	< -60	-4.6
0.114	20.6	78.9	49.0	28.4	11.9	53.2	-33	< -60	-4.7
0.144	21.6	80.4	49.1	27.5	12.0	53.5	-33	< -60	-4.7
0.181	22.6	81.7	49.1	26.5	12.2	53.7	-33	< -60	-4.7
0.231	23.6	83.0	49.2	25.6	12.3	53.9	-33	< -60	-4.7
0.292	24.7	84.3	49.3	24.6	12.4	54.2	-33	< -60	-4.7

**@ f=425MHz**

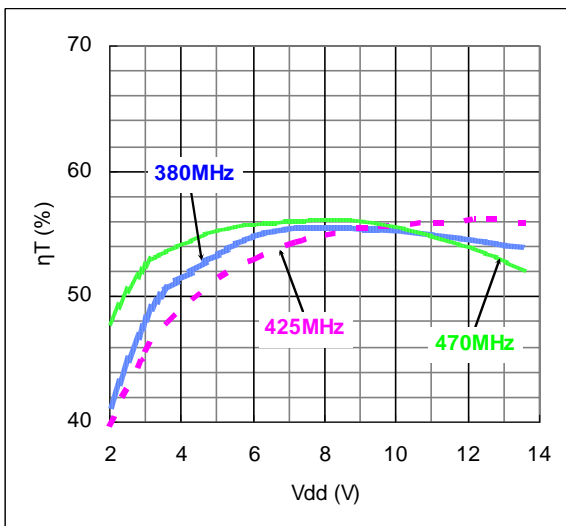
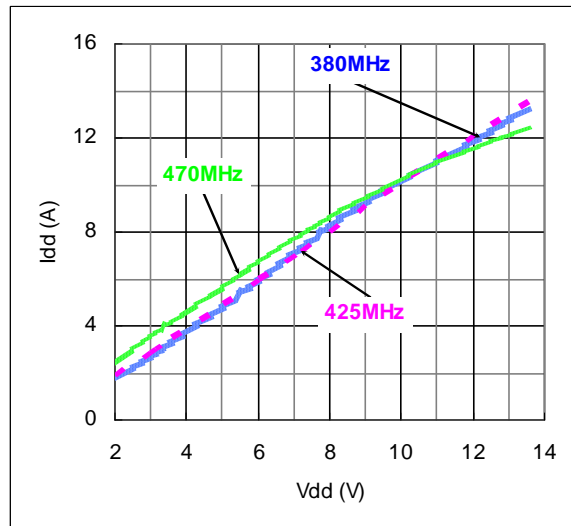
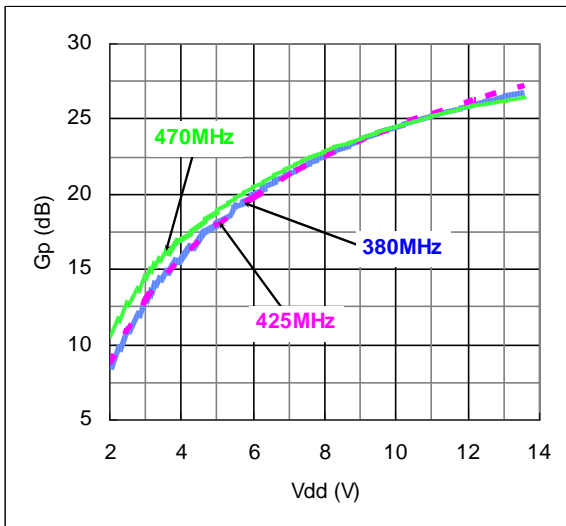
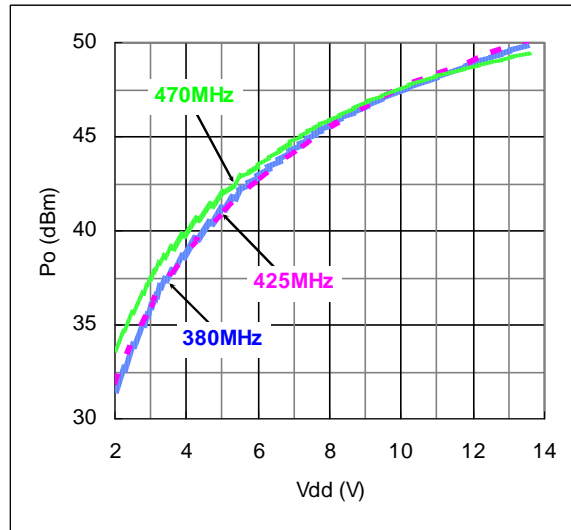
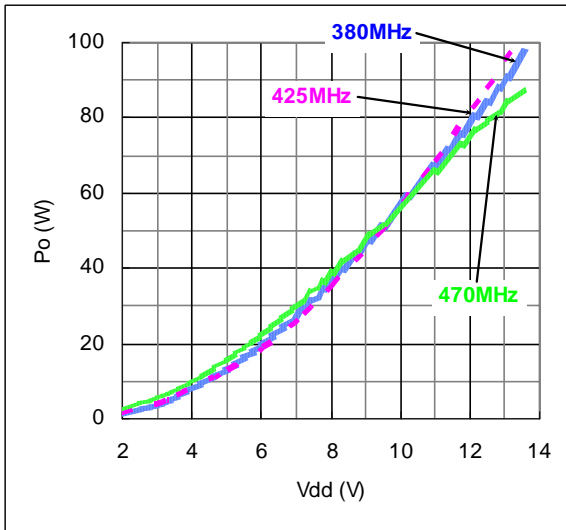
Pi (W)	Pi (dBm)	Po (W)	Po (dBm)	Gp (dB)	Idd (A)	$\eta_T$ (%)	2fo (dBc)	3fo (dBc)	R.L. (dB)
0.003	5.0	5.81	37.6	32.7	3.01	15.3	-38	< -50	-10.2
0.005	7.2	9.3	39.7	32.5	3.73	19.7	-38	< -50	-14.0
0.009	9.3	15.1	41.8	32.4	4.70	25.4	-38	< -60	-20.2
0.014	11.4	24.2	43.8	32.5	5.92	32.3	-38	< -60	-20.4
0.022	13.4	38.0	45.8	32.4	7.49	40.3	-38	< -60	-17.0
0.035	15.4	54.3	47.4	31.9	9.19	47.0	-40	< -60	-15.8
0.056	17.4	69.8	48.4	31.0	10.8	51.7	-43	< -60	-15.8
0.090	19.6	81.1	49.1	29.5	11.9	54.3	-45	< -60	-16.8
0.114	20.6	84.1	49.3	28.7	12.3	54.9	-46	< -60	-17.1
0.142	21.5	85.9	49.3	27.8	12.4	55.2	-47	< -60	-15.7
0.177	22.5	86.9	49.4	26.9	12.5	55.4	-47	< -60	-14.6
0.224	23.5	87.5	49.4	25.9	12.6	55.5	-47	< -60	-13.6
0.280	24.5	87.9	49.4	25.0	12.6	55.6	-47	< -60	-12.9

**@ f=470MHz**

Pi (W)	Pi (dBm)	Po (W)	Po (dBm)	Gp (dB)	Idd (A)	$\eta_T$ (%)	2fo (dBc)	3fo (dBc)	R.L. (dB)
0.003	4.9	1.52	31.8	26.9	1.85	6.5	-51	< -50	-10.3
0.005	7.1	2.48	33.9	26.8	2.19	8.9	-52	< -51	-15.1
0.008	9.3	4.12	36.2	26.9	2.70	12.1	-53	< -53	-25.8
0.014	11.3	6.90	38.4	27.1	3.40	16.1	-53	< -55	-16.6
0.022	13.3	11.6	40.7	27.3	4.33	21.3	-54	< -60	-14.9
0.035	15.4	19.9	43.0	27.6	5.61	28.1	-54	< -60	-14.1
0.055	17.4	32.8	45.2	27.7	7.19	36.3	-54	< -60	-13.7
0.089	19.5	51.1	47.1	27.6	9.11	44.7	-56	< -60	-13.6
0.112	20.5	60.1	47.8	27.3	10.00	48.0	-58	< -60	-12.9
0.140	21.5	68.4	48.4	26.9	10.82	50.5	-59	< -60	-12.9
0.177	22.5	75.5	48.8	26.3	11.5	52.4	-61	< -60	-12.9
0.223	23.5	81.5	49.1	25.6	12.1	53.8	-62	< -60	-12.9
0.286	24.6	86.1	49.4	24.8	12.6	54.6	-63	< -60	-13.0

### 5-3. Pout vs. Vdd characteristics

@ Pi=0.2W (=23dBm), Idq=1.1A(Vgg=2.67V), f=380MHz, 425MHz, 470MHz



**5-3-1. Pout vs. Vdd characteristics data**

[Conditions ; Pi=0.2W (=23dBm), Idq=1.1A (Vgg=2.67V, RD04HMS2 ; 0.1A, RD70HUF2 ; 1A)]

**@ f=380MHz**

Vdd (V)	Po (W)	Po (dBm)	Gp (dB)	Idd (A)	$\eta_T$ (%)
2.0	1.4	31.5	8.5	1.73	41.3
3.0	3.9	36.0	12.9	2.72	48.3
3.6	6.1	37.8	14.8	3.33	50.6
5.0	13.0	41.1	18.1	4.85	53.5
6.0	19.7	43.0	19.9	5.98	54.9
7.2	29.2	44.7	21.6	7.32	55.6
8.0	36.6	45.6	22.6	8.22	55.6
9.5	51.2	47.1	24.1	9.7	55.4
11.0	66.8	48.3	25.2	11.0	55.0
12.5	84.1	49.3	26.2	12.3	54.5
13.6	97.3	49.9	26.9	13.3	54.0

**@ f=425MHz**

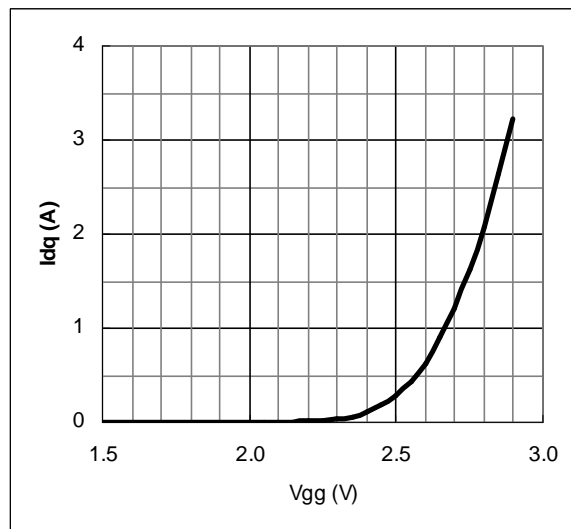
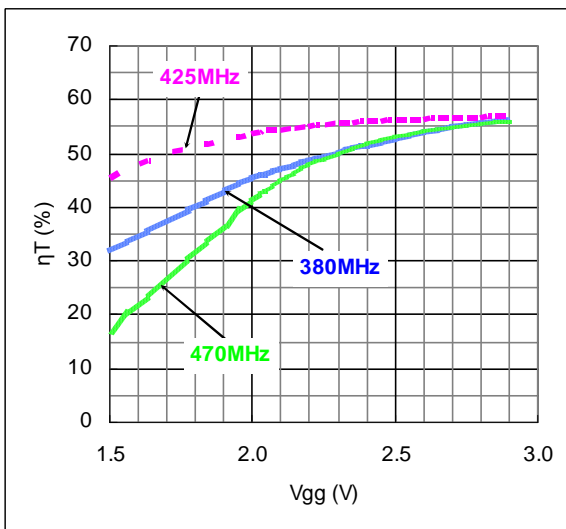
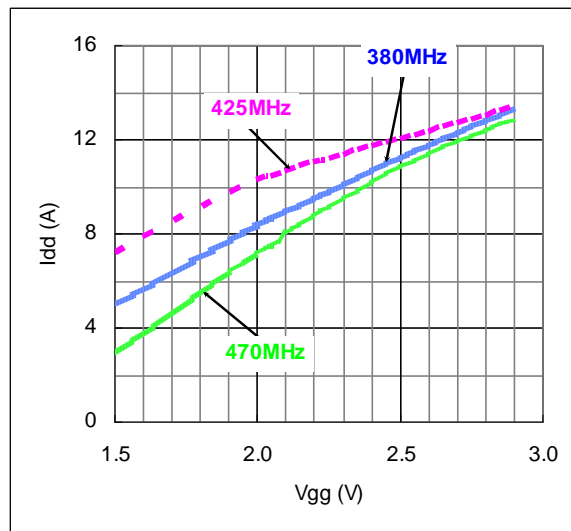
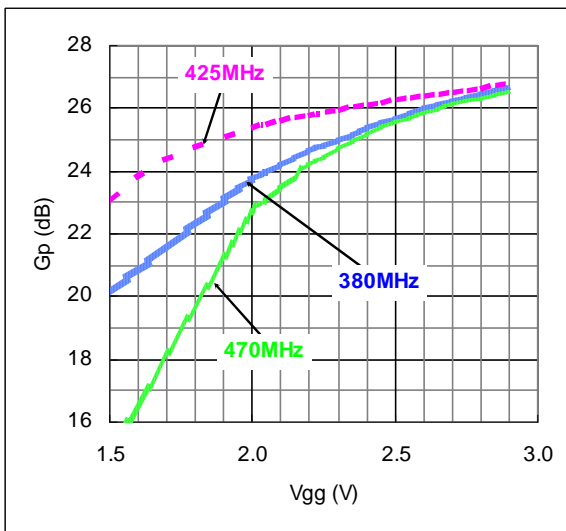
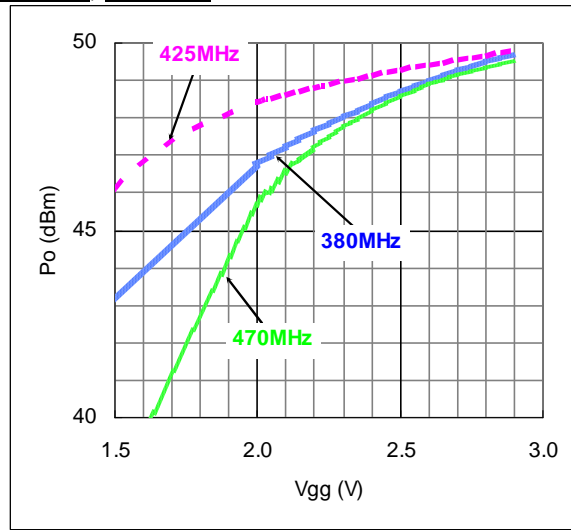
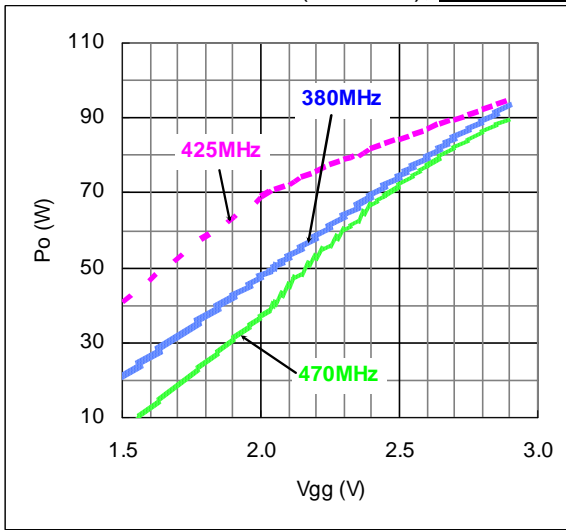
Vdd (V)	Po (W)	Po (dBm)	Gp (dB)	Idd (A)	$\eta_T$ (%)
2.0	1.5	31.8	8.8	1.91	39.6
3.0	3.9	35.9	12.9	2.86	45.5
3.6	6.0	37.8	14.7	3.47	48.0
5.0	12.6	41.0	18.0	4.90	51.5
6.0	18.9	42.8	19.7	5.94	52.9
7.2	28.1	44.5	21.5	7.18	54.3
8.0	35.2	45.5	22.4	8.01	54.9
9.5	50.6	47.0	24.0	9.56	55.6
11.0	68.2	48.3	25.3	11.1	55.9
12.5	87.9	49.4	26.4	12.5	56.1
13.6	103.3	50.1	27.1	13.6	55.8

**@ f=470MHz**

Vdd (V)	Po (W)	Po (dBm)	Gp (dB)	Idd (A)	$\eta_T$ (%)
2.0	2.3	33.6	10.6	2.41	47.9
3.0	5.5	37.4	14.4	3.52	52.4
3.6	8.1	39.1	16.0	4.17	53.6
5.0	15.7	42.0	18.9	5.66	55.2
6.0	22.3	43.5	20.5	6.69	55.7
7.2	31.8	45.0	22.0	7.87	56.0
8.0	38.6	45.9	22.8	8.59	56.2
9.5	52.1	47.2	24.1	9.82	55.8
11.0	65.8	48.2	25.2	10.92	54.9
12.5	79.3	49.0	26.0	11.9	53.4
13.6	87.9	49.4	26.4	12.4	52.1

### 5-4. Pout vs. Vgg characteristics

@ Vdd=12.5V, Pi=0.2W (=23dBm), f=380MHz, 425MHz, 470MHz





**5-4-1. Pout vs. Vgg characteristics data**

[Conditions ; Pi=0.2W (=23dBm), Vdd=12.5V]

**@ f=380MHz**

Vgg (V)	Idq (A)	Pi (W)	Pi (dBm)	Po (W)	Po (dBm)	Gp (dB)	Idd (A)	$\eta_T$ (%)
1.50	0	0.200	23.0	20.3	43.1	20.1	5.00	32.2
2.00	0.001	0.200	23.0	47.8	46.8	23.8	8.38	45.4
2.10	0.004	0.200	23.0	53.1	47.3	24.2	9.0	47.2
2.20	0.012	0.200	23.0	58.5	47.7	24.7	9.5	48.9
2.30	0.04	0.201	23.0	63.8	48.1	25.0	10.1	50.3
2.40	0.11	0.200	23.0	69.2	48.4	25.4	10.7	51.6
2.50	0.28	0.200	23.0	74.5	48.7	25.7	11.3	52.9
2.60	0.62	0.200	23.0	79.6	49.0	26.0	11.8	54.0
2.65	0.90	0.200	23.0	82.2	49.2	26.1	12.1	54.5
2.70	1.20	0.200	23.0	84.7	49.3	26.3	12.3	55.0
2.75	1.63	0.200	23.0	87.1	49.4	26.4	12.6	55.4
2.80	2.07	0.200	23.0	89.3	49.5	26.5	12.8	55.8
2.85	2.64	0.200	23.0	91.6	49.6	26.6	13.1	56.1
2.90	3.22	0.201	23.0	93.8	49.7	26.7	13.32	56.4

**@ f=425MHz**

Vgg (V)	Idq (A)	Pi (W)	Pi (dBm)	Po (W)	Po (dBm)	Gp (dB)	Idd (A)	$\eta_T$ (%)
1.50	0	0.201	23.0	40.7	46.1	23.1	7.16	45.2
2.00	0.001	0.201	23.0	68.7	48.4	25.3	10.25	53.5
2.10	0.004	0.201	23.0	72.3	48.6	25.6	10.6	54.2
2.20	0.012	0.200	23.0	75.5	48.8	25.8	11.0	54.8
2.30	0.04	0.200	23.0	78.5	49.0	25.9	11.4	55.3
2.40	0.11	0.200	23.0	81.5	49.1	26.1	11.7	55.7
2.50	0.28	0.201	23.0	84.1	49.3	26.2	12.0	56.1
2.60	0.62	0.201	23.0	86.7	49.4	26.4	12.3	56.3
2.65	0.90	0.200	23.0	88.1	49.5	26.4	12.5	56.4
2.70	1.20	0.201	23.0	89.3	49.5	26.5	12.7	56.5
2.75	1.63	0.201	23.0	90.8	49.6	26.6	12.8	56.6
2.80	2.07	0.201	23.0	91.8	49.6	26.6	13.0	56.6
2.85	2.64	0.201	23.0	93.3	49.7	26.7	13.2	56.8
2.90	3.22	0.200	23.0	94.4	49.8	26.7	13.32	56.8

**@ f=470MHz**

Vgg (V)	Idq (A)	Pi (W)	Pi (dBm)	Po (W)	Po (dBm)	Gp (dB)	Idd (A)	$\eta_T$ (%)
1.50	0	0.201	23.0	6.3	38.0	15.0	2.97	16.8
2.00	0.001	0.201	23.0	37.2	45.7	22.7	7.15	41.3
2.10	0.004	0.201	23.0	44.9	46.5	23.5	8.0	44.8
2.20	0.012	0.200	23.0	52.5	47.2	24.2	8.8	47.7
2.30	0.04	0.201	23.0	59.6	47.8	24.7	9.5	50.0
2.40	0.11	0.201	23.0	66.2	48.2	25.2	10.2	51.8
2.50	0.28	0.201	23.0	72.1	48.6	25.5	10.8	53.1
2.60	0.62	0.201	23.0	77.4	48.9	25.9	11.4	54.2
2.65	0.90	0.201	23.0	79.6	49.0	26.0	11.7	54.5
2.70	1.20	0.201	23.0	81.8	49.1	26.1	11.9	54.9
2.75	1.63	0.201	23.0	84.1	49.3	26.2	12.2	55.2
2.80	2.07	0.201	23.0	86.1	49.4	26.3	12.4	55.5
2.85	2.64	0.201	23.0	88.1	49.5	26.4	12.6	55.8
2.90	3.22	0.201	23.0	89.7	49.5	26.5	12.85	56.0